



#### 40V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-40V	$60m\Omega @ V_{GS} = -10V$	-6.4A
-40 V	$100m\Omega @ V_{GS} = -4.5V$	-5.0A

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

## Features and Benefits

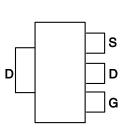
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

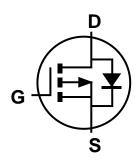
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (63)
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top



Equivalent Circuit

#### Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP4A16GTA	ZXMP4A16	7	12	1,000
ZXMP4A16GTC	ZXMP4A16	13	12	4,000

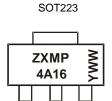
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Haloger- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZXMP4A16 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage Gate-Source Voltage			Symbol	Value	Units
			V <sub>DSS</sub>	-40	V
			V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$ (Note 6) $T_A = +70^{\circ}C$ (Note 6) $T_A = +25^{\circ}C$ (Note 5)	ID	-6.4 -5.1 -4.6	А
Maximum Body Diode Forward Current (Note 6)			Is	-5.2	A
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	-21	A
Pulsed Source Current (Note 7)			I <sub>SM</sub>	-21	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 5)	PD	2.0 16	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	PD	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient	Steady state (Note 5)	Р	62.5	°C/W
	Steady state (Note 6)	R <sub>0JA</sub>	32	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	•					-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_		V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1.0	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	•		•		•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—		V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	Deserve	_	_	60		V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A	
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>	_	_	100	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9A	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>		-0.85	-1.2	V	$V_{GS} = 0V, I_{S} = -3.4A$	
Forward Transconductance (Notes 8 & 10)	<b>g</b> <sub>fs</sub>		8.85		S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.8A	
DYNAMIC CHARACTERISTICS (Note 10)			•		•	•	
Input Capacitance	Ciss		1,007			$V_{DS} = -20V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	C <sub>oss</sub>	_	130		pF		
Reverse Transfer Capacitance	Crss	_	85				
Total Gate Charge (V <sub>GS</sub> = -5.0V)	Qg		13.6			$V_{DS} = -20V, I_D = -3.8A,$	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg		26.1		nC		
Gate-Source Charge	Qgs		2.8		nc		
Gate-Drain Charge	Q <sub>gd</sub>		4.8				
Turn-On Delay Time	t <sub>D(on)</sub>		2.33			$V_{GS} = -10V, V_{DD} = -20V, R_G = 6.0\Omega,$ $I_{D} = -1.0A$	
Turn-On Rise Time	tr		8.84		nS		
Turn-Off Delay Time	t <sub>D(off)</sub>		29.18				
Turn-Off Fall Time	tf		12.54				
Body Diode Reverse Recovery Time	t <sub>rr</sub>		27.2		nS		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	_	25.4		nC	−I <sub>F</sub> = -3A, dI/dt = 100A/μs	

 Notes:
 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

 6. For a device surface mounted on FR4 PCB measured at t ≤10 secs.

 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width limited by maximum junction temperature.

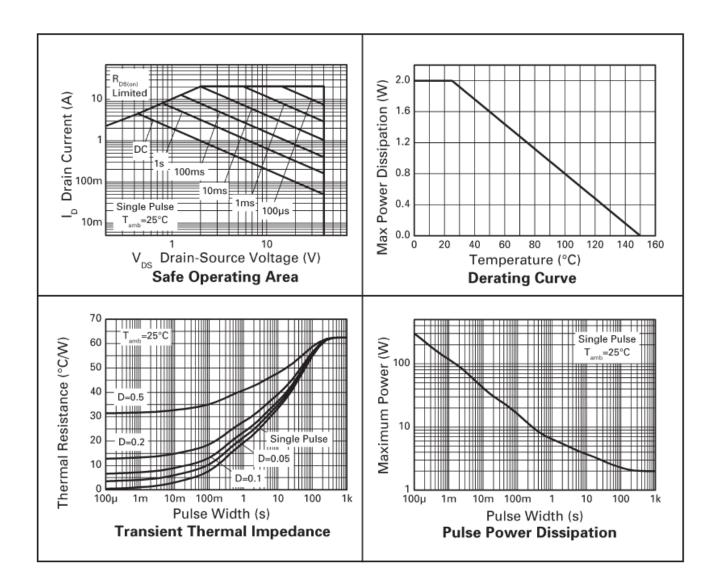
8. Measured under pulsed conditions. Width $\leq$ 300µs. Duty cycle  $\leq$  2%.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

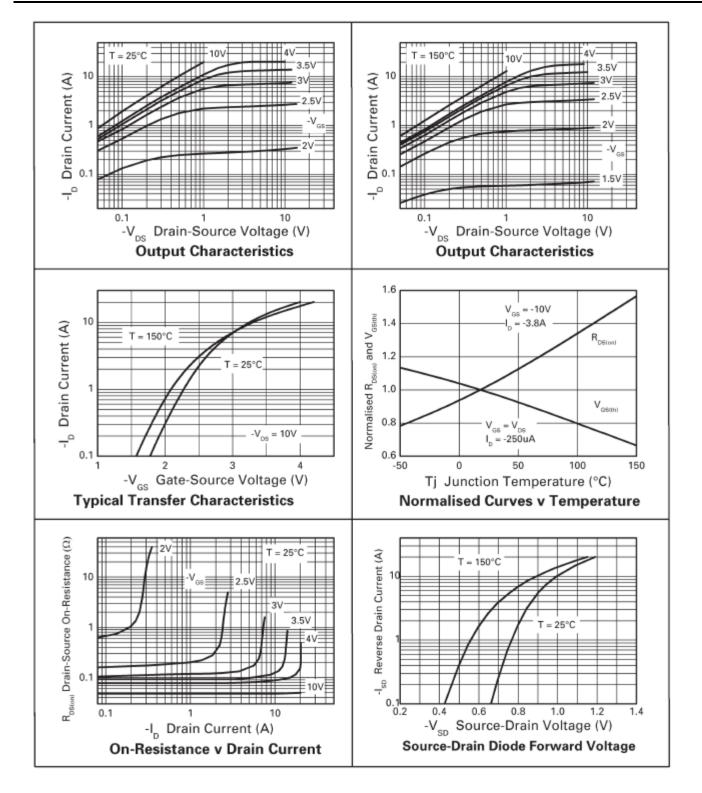


# **Typical Characteristics**



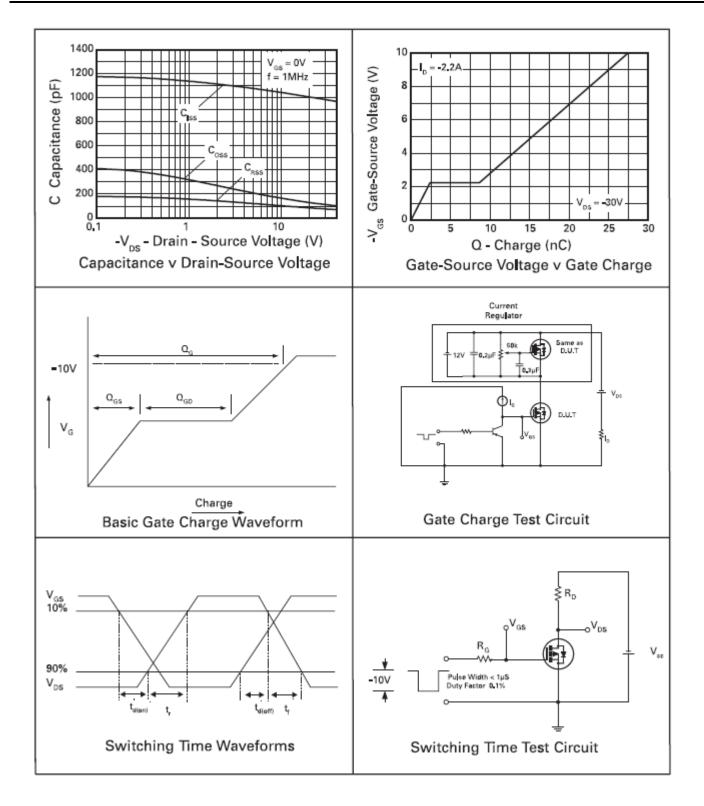


## Typical Characteristics (continued)





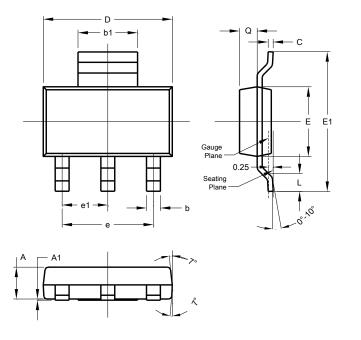
## Typical Characteristics (continued)





## **Package Outline Dimensions**

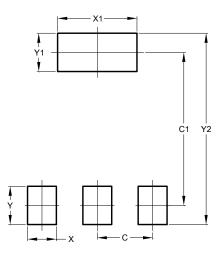
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [	All Dimensions in mm				

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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